





#### **DUAL 15V NPN LOW SATURATION TRANSISTORS**

#### **Features and Benefits**

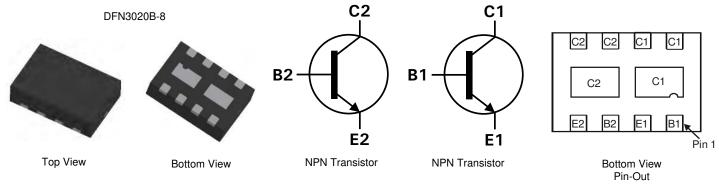
- BV<sub>CEO</sub> > 15V
- I<sub>C</sub> = 4.5A Continuous Collector Current
- Low Saturation Voltage (100mV max @ 1A)
- R<sub>SAT</sub> = 45 mΩ for a Low Equivalent On-Resistance
- h<sub>FE</sub> specified up to 12A for high current gain hold up
- Dual NPN saving footprint and component count
- Low profile 0.8mm high package for thin applications
   R<sub>BJA</sub> efficient, 40% lower than SOT26
- 6mm² footprint, 50% smaller than TSOP6 and SOT26
- Lead-Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: DFN3020B-8
- Case Material: Molded Plastic. "Green" Molding Compound.
- Terminals: Pre-Plated NiPdAu leadframe
- UL Flammability Rating 94V-0
- Nominal Package Height: 0.8mm
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.013 grams (approximate)

## **Applications**

- DC-DC Converters
- · Charging circuits
- Motor control
- Power switches
- Portable applications



**Equivalent Circuit** 

## **Ordering Information**

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTD617MCTA	DAA	7	8	3000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

# **Marking Information**



DAA = Product type marking code Top view, dot denotes pin 1





# Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit	
Collector-Base Voltage		$V_{CBO}$	40		
Collector-Emitter Voltage		$V_{CEO}$	15	V	
Emitter-Base Voltage		V <sub>EBO</sub>	7		
Peak Pulse Current		Ісм	15		
Continuous Collector Current	(Notes 3 & 6)	I-	4.5	^	
Continuous Collector Current	(Notes 4 & 6)	IC	5	] ^	
Base Current		$I_{B}$	1		

# Thermal Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
	(Notes 3 & 6)		1.5 12		
Power Dissipation	(Notes 4 & 6)		2.45 19.6	W	
Linear Derating Factor	(Notes 5 & 6)	P <sub>D</sub>	1.13 8	mW/°C	
	(Notes 5 & 7)		1.7 13.6		
	(Notes 3 & 6)		83.3		
Thermal Desistance Junation to Ambient	(Notes 4 & 6)		51.0		
Thermal Resistance, Junction to Ambient	(Notes 5 & 6)	$R_{\theta JA}$	111	°C/W	
	(Notes 5 & 7)		73.5		
Thermal Resistance, Junction to Lead (Notes 6 & 8)		$R_{ heta JL}$	17.1		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

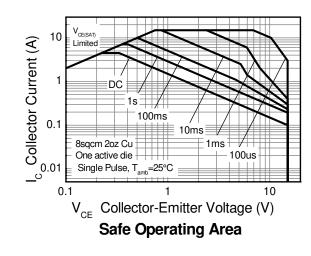
#### Notes:

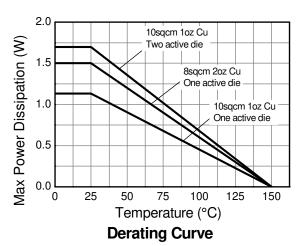
- 3. For a dual device surface mounted on 28mm x 28mm (8cm²) FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The heatsink is split in half with the exposed collector pads connected to each half.
- 4. Same as note (3), except the device is measured at t <5 sec.

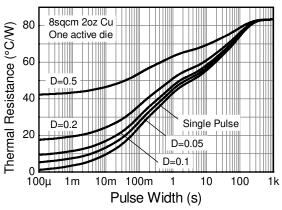
  5. Same as note (3), except the device is surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper.
- 6. For a dual device with one active die.
- 7. For dual device with 2 active die running at equal power.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).

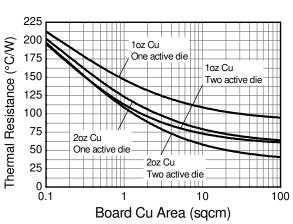


### **Thermal Characteristics**



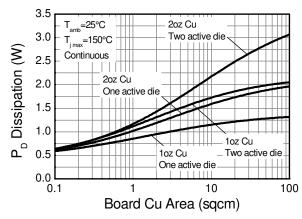






### **Transient Thermal Impedance**

Thermal Resistance v Board Area



**Power Dissipation v Board Area** 





# Electrical Characteristics @TA = 25°C unless otherwise specified

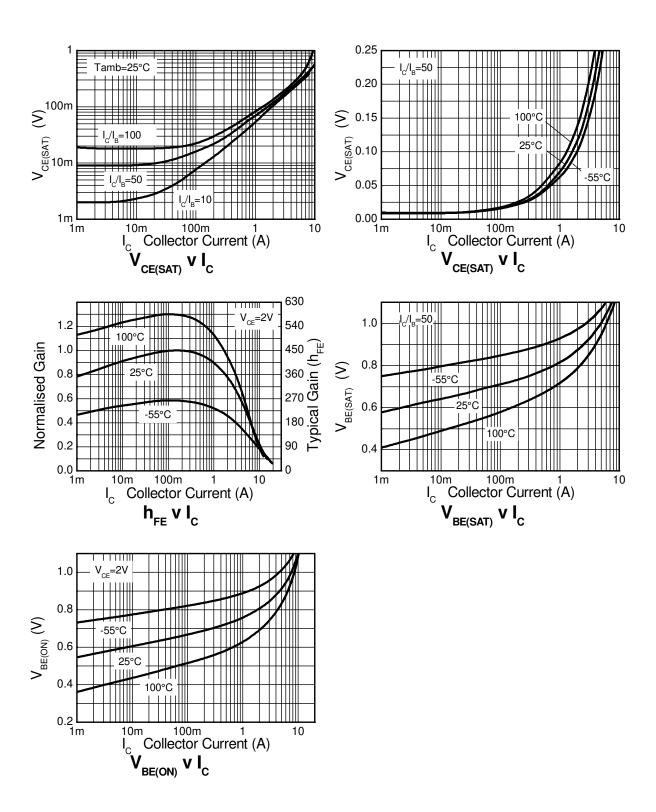
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	40	70	-	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	15	18	-	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.2	-	V	$I_E = 100\mu A$
Collector Cutoff Current	I <sub>CBO</sub>	-	-	100	nA	V <sub>CB</sub> = 30V
Emitter Cutoff Current	I <sub>EBO</sub>	-	-	100	. nA	$V_{EB} = 6V$
Collector Emitter Cutoff Current	I <sub>CES</sub>	-	-	100	nA	V <sub>CES</sub> = 12V
		200	415	-	-	$I_C = 10mA, V_{CE} = 2V$
	h <sub>FE</sub>	300	450	-	-	$I_C = 200 \text{mA}, V_{CE} = 2V$
Static Forward Current Transfer Ratio (Note 9)		200	320	-	-	$I_C = 3A$ , $V_{CE} = 2V$
		150	240	-	-	$I_C = 5A, V_{CE} = 2V$
		-	80	-	-	I <sub>C</sub> = 12A, V <sub>CE</sub> = 2V
		-	8	14	mV	$I_C = 0.1A$ , $I_B = 10mA$
		-	70	100	mV	$I_C = 1A$ , $I_B = 10mA$
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	-	165	200	mV	$I_C = 3A$ , $I_B = 50mA$
	(-1.1)	-	240	310	mV	$I_C = 4.5A$ , $I_B = 50mA$
		-	200	-	mV	I <sub>C</sub> =4.5A, I <sub>B</sub> = 100mA
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	-	0.88	0.96	V	I <sub>C</sub> = 4.5A, V <sub>CE</sub> = 2V
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	-	0.94	1.05	V	$I_C = 4.5A, I_B = 50mA$
Output Capacitance	$C_{obo}$	-	30	40	pF	V <sub>CB</sub> = 10V. f = 1MHz
Transition Frequency	f <sub>T</sub>	80	120	-	MHz	$V_{CE} = 10V, I_{C} = 50mA,$ f = 100MHz
Turn-on Time	t <sub>on</sub>	-	120	-	ns	V <sub>CC</sub> = 10V, I <sub>C</sub> = 1A
Turn-off Time	t <sub>off</sub>	-	160	-	ns	$I_{B1} = I_{B2} = 10 \text{mA}$

Notes: 9. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%



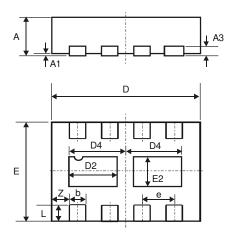


# **Typical Electrical Characteristics**



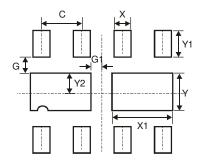


# **Package Outline Dimensions**



DFN3020B-8					
Dim	Min	Max	Тур		
Α	0.77	0.83	0.80		
A1	0	0.05	0.02		
<b>A3</b>	1	1	0.15		
b	0.25	0.35	0.30		
D	2.95	3.075	3.00		
D2	0.82	1.02	0.92		
D4	1.01	1.21	1.11		
е	-	-	0.65		
Е	1.95	2.075	2.00		
E2	0.43	0.63	0.53		
L	0.25	0.35	0.30		
Z	-	-	0.375		
All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)		
С	0.650		
G	0.285		
G1	0.090		
Х	0.400		
X1	1.120		
Υ	0.730		
Y1	0.500		
Y2	0.365		





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